



### Very-Low-Power Two-Output PCIe Clock Buffer With On-Chip Termination

#### **Features**

- → 3.3V Supply Voltage
- → HCSL Input of 100MHz; Also supports 50MHz, 125MHz, or 133.33MHz via SMBus
- → Two Differential Low-Power HCSL Outputs with On-Chip Termination
- → Default  $Z_{OUT} = 100Ω$
- → Spread-Spectrum Tolerant
- → Individual Output Enable
- → Programmable Slew Rate and Output Amplitude for each output
- → Differential Outputs Blocked until PLL is Locked
- → Strapping Pins or SMBus for Configuration
- → Differential output-to-output skew <50ps
- → Very low jitter outputs
  - ♦ Differential cycle-to-cycle jitter <50ps
  - ♦ PCIe Gen1/Gen2/Gen3/Gen4/Gen5 CC compliant
  - ♦ PCIe Gen 2 and 3 SRiS and SRnS compliant
- → Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- → Halogen and Antimony Free. "Green" Device (Note 3)
- → For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

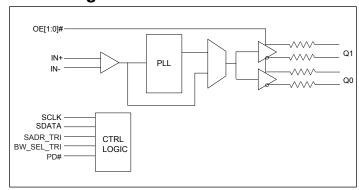
- → Packaging (Pb-free & Green):
  - 24-lead 4mm × 4mm TQFN

### **Description**

The PI6CB33201 is a two-output very-low-power PCIe Gen1/Gen2/Gen3/Gen4/Gen5 clock buffer. It takes a reference input to fanout two 100MHz low-power differential HCSL outputs with on-chip terminations. The on-chip termination can save eight external resistors and make layout easier. Individual OE pin for each output provides easier power management.

It uses Diodes proprietary PLL design to achieve very-low jitter that meets PCIe Gen1/Gen2/Gen3/Gen4/Gen5 requirements. Other than PCIe 100MHz support, this device also support Ethernet application with 50MHz, 125MHz, and 133.33MHz via SMBus. It provides various options such as different slew rate and amplitude through SMBUS, so users can configure the device easily to get the optimized performance for their individual boards.

### **Block Diagram**



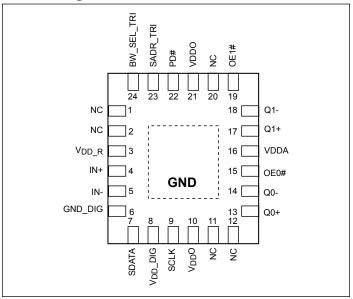
#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





# **Pin Configuration**



**Pin Description** 

Pin Number	Pin Name	Ту	pe	Description
1	NC	_	_	Internal connected for feedback loop. Do not connect this pin.
2	NC	_	_	Internal connected for feedback loop. Do not connect this pin.
3	V <sub>DD</sub> _R	Power	_	Power supply for input differential buffers
4	IN+	Input	_	Differential true clock input
5	IN-	Input	_	Differential complementary clock input
6	GND_DIG	Power	_	Ground for digital circuitry
7	SDATA	Input/ Output	CMOS	SMBUS data line, 3.3V tolerant
8	V <sub>DD</sub> _DIG	Power	_	Power supply for digital circuitry, nominal 3.3V
9	SCLK	Input	CMOS	SMBUS clock input, 3.3V tolerant
10	$V_{ m DDO}$	Power	_	Power supply for differential outputs
11	NC	_	_	Do not connect this pin.
12	NC	_	_	Do not connect this pin.
13	Q0+	Output	HCSL	Differential true clock output
14	Q0-	Output	HCSL	Differential complementary clock output
15	OE0#	Input	CMOS	Active-low input for enabling Q0 pair. This pin has an internal pulldown.
13	OE0#	Input	CIVIOS	1 = disable outputs, 0 = enable outputs
16	$V_{DDA}$	Power	_	Power supply for analog circuitry
17	Q1+	Output	HCSL	Differential true clock output





Pin Description Cont.

203011	in Description com:							
Pin Number	Pin Name	Туре		Description				
18	Q1-	Output	HCSL	Differential complementary clock output				
19	OE1#	Input	CMOS	Active-low input for enabling Q1 pair. This pin has an internal pulldown. 1 = disable outputs, 0 = enable outputs				
20	NC	_	_	Do not connect this pin.				
21	$V_{\mathrm{DDO}}$	Power	_	Power supply for differential outputs				
22	PD#	Input	CMOS	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has an internal pullup resistor.				
23	SADR_TRI	Input	Tri-level	Latch to select SMBus Address. This pin has an internal pulldown.				
24	BW_SEL_TRI	Input	Tri-level	Latch to select low-loop bandwidth, bypass PLL, and high-loop bandwidth. This pin has both internal pullup and pulldown				
_	EPAD	Power	_	Connect to Ground.				





### **SMBus Address Selection Table**

	SADR	Address	+Read/Write Bit
	0	1101011	X
State of SADR on first application of PD#	M	1101100	X
	1	1101101	X

### **Power Management Table**

PD#	IN	SMBus OE bit	OEn#	Qn+	Qn-	PLL Status
0	X	X	X	Low <sup>(2)</sup>	Low <sup>(2)</sup>	Off
1	Running	0	X	Low <sup>(2)</sup>	Low <sup>(2)</sup>	On <sup>(1)</sup>
1	Running	1	0	Running	Running	On <sup>(1)</sup>
1	Running	1	1	Low <sup>(2)</sup>	Low <sup>(2)</sup>	On <sup>(1)</sup>

#### Note:

# **PLL Operating Mode Select Table**

BW_SEL_TRI	Operating Mode	Byte1 [7:6] Readback	Bytel [4:3] Control
0	PLL with Low Bandwidth	00	00
M	PLL Bypass	01	01
1	PLL with High Bandwidth	11	11

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# **Frequency Select Table**

Freq. Select Byte 3 [4:3]	IN (MHz)	Qn (MHz)
00 (default)	100	100
01	50	50
10	125	125
11	133.33	133.33

<sup>1.</sup> If PLL Bypass mode is selected, the PLL will be off and outputs will be running.

<sup>2.</sup> The output state is set by B11[1:0] (Low/Low default).





### **Maximum Ratings**

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature65°C to +150°C
Supply Voltage to Ground Potential, $V_{DDxx}$ 0.5V to +4.6V
Input Voltage $-0.5V$ to $V_{DD+0.5V}$ , not exceed 4.6V
SMBus, Input High Voltage
ESD Protection (HBM)2000 V
Junction Temperature

#### Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

# **Operating Conditions**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
$V_{DDO,} \\ V_{DDA,} \\ V_{DD\_}R, \\ V_{DD\_}DIG$	Power Supply Voltage	_	3.135	3.3	3.465	V
$I_{DDA}$	Analog Power Supply Current	$V_{DDA}$ , PLL mode, All outputs active @ 100MHz	_	21	25	mA
I <sub>DD_DIG</sub>	Digital Power Supply Current	V <sub>DD_DIG</sub> , All outputs active @ 100MHz	_	0.1	1	mA
I <sub>DDO+R</sub>	Power Supply Current for Inputs and Outputs <sup>(2)</sup>	V <sub>DDO</sub> + V <sub>DD_R</sub> , PLL mode, All outputs active @ 100MHz	_	38	44	mA
I <sub>DDA_PD</sub>	Analog Power Supply Power Down <sup>(1)</sup> Current	V <sub>DDA</sub> , PLL mode, All outputs LOW/LOW	_	0.5	1	mA
I <sub>DD_DIG_PD</sub>	Power Supply Power Down <sup>(1)</sup> Current	V <sub>DD_DIG</sub> , All outputs LOW/LOW	_	0.1	1	mA
I <sub>DDO_R_PD</sub>	Power Supply Current Power Down <sup>(1)</sup> for Inputs and Outputs	V <sub>DDO</sub> , V <sub>DD_R</sub> All outputs LOW/ LOW	_	1	2	mA
T <sub>A</sub>	Ambient Temperature	Industrial grade	-40	_	85	°C

#### Note:

- 1. Input clock is not running.
- 2. Outputs drive 5 inch trace.

## **Input Electrical Characteristics**

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
R <sub>pu</sub>	Internal Pullup Resistance	-		120	_	kΩ
R <sub>dn</sub>	Internal Pulldown Resistance	_	_	120	_	kΩ
L <sub>PIN</sub>	Pin Inductance	_	_	_	7	nН





### **SMBus Electrical Characteristics**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V <sub>DDSMB</sub>	Nominal Bus Voltage	_	2.7	_	3.6	V
	V <sub>IHSMB</sub> SMBus Input High Voltage	SMBus, $V_{DDSMB} = 3.3V$	2.1		3.6	
V <sub>IHSMB</sub>		SMBus, V <sub>DDSMB</sub> < 3.3V	0.65 V <sub>DDSMB</sub>	_	_	V
3.7	SMBus Input Low Voltage	SMBus, $V_{DDSMB} = 3.3V$	_	_	0.8	V
V <sub>ILSMB</sub>		SMBus, V <sub>DDSMB</sub> < 3.3V	_	_	0.8	V
I <sub>SMBSINK</sub>	SMBus Sink Current	SMBus, at V <sub>OLSMB</sub>	4	_	_	mA
V <sub>OLSMB</sub>	SMBus Output Low Voltage	SMBus, at I <sub>SMBSINK</sub>	_	_	0.4	V
$f_{MAXSMB}$	SMBus Operating Frequency	Maximum frequency	_	_	500	kHz
t <sub>RMSB</sub>	SMBus Rise Time	(Max V <sub>IL</sub> - 0.15) to (Min V <sub>IH</sub> + 0.15)	_	_	1000	ns
t <sub>FMSB</sub>	SMBus Fall Time	(Min $V_{IH}$ + 0.15) to (Max $V_{IL}$ - 0.15)	_	_	300	ns

### **LVCMOS DC Electrical Characteristics**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V <sub>IH</sub>	Input High Voltage	Single-ended inputs, except SMBus	0.75 V <sub>DD</sub>	_	V <sub>DD</sub> +0.3	V
$V_{IM}$	Input Mid Voltage	SADR_TRI, BW_SEL_TRI	$0.4 \mathrm{V}_\mathrm{DD}$	$0.5 \mathrm{V}_\mathrm{DD}$	$0.6 \mathrm{V}_\mathrm{DD}$	V
$V_{\rm IL}$	Input Low Voltage	Single-ended inputs, except SMBus	-0.3	_	0.25 V <sub>DD</sub>	V
$I_{IH}$	Input High Current	Single-ended inputs, $V_{IN} = V_{DD}$	_	_	5	μΑ
$I_{IL}$	Input Low Current	Single-ended inputs, $V_{\rm IN} = 0V$	-5	_	_	μΑ
$I_{IH}$	Input High Current	Single-ended inputs with pullup/pulldown resistor, $V_{\mathrm{IN}} = V_{\mathrm{DD}}$	_	_	50	μΑ
$I_{IL}$	Input Low Current	Single-ended inputs with pullup/pulldown resistor, $V_{\rm IN}$ = 0V	-50	_	_	μΑ
C <sub>IN</sub>	Input Capacitance	_	1.5	_	5	pF





### **LVCMOS AC Electrical Characteristics**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
t <sub>OELAT</sub>	Output Enable Latency	Q start after OE# assertion Q stop after OE# de-assertion	1	_	3	clocks
t <sub>PDLAT</sub>	PD# De-assertion	Differential outputs enable after PD# de-assertion	_	20	300	μs

## HCSL Input Characteristics(1)

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V <sub>IHDIF</sub>	Diff. Input High Voltage <sup>(3)</sup>	IN+, IN-, single-end measurement	600	800	1150	mV
$V_{ILDIF}$	Diff. Input Low Voltage <sup>(3)</sup>	IN+, IN-, single-end measurement	-300	0	300	mV
V <sub>COM</sub>	Diff. Input Common Mode Voltage		150		900	mV
V <sub>SWING</sub>	Diff. Input Swing Voltage	Peak to peak value (V <sub>IHDIF</sub> - V <sub>ILDIF)</sub>	300		2900	mV
$f_{INBP}$	Input Frequency	PLL Bypass mode	1		200	MHz
$f_{\rm IN100}$	Input Frequency	100MHz PLL	99.9	100	100.1	MHz
f <sub>IN133</sub>	Input Frequency	133MHz PLL	133.2	133.33	133.46	MHz
f <sub>IN125</sub>	Input Frequency	125MHz PLL	124.87	125	125.12	MHz
f <sub>IN50</sub>	Input Frequency	50MHz PLL	49.95	50	50.05	MHz
f <sub>MODI</sub> - PCIe	Input SS Modulation Freq. PCIe	Allowable frequency for PCIe applications (Triangular Modulation)	30		33	kHz
f <sub>MODIN</sub> -	Input SS Modulation Freq. non-PCIe	Allowable frequency for non-PCIe applications (Triangular Modulation)	0		46	kHz
t <sub>STAB</sub>	Clock stabilization	From V <sub>DD</sub> Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock		0.75	1.0	ms
t <sub>RF</sub>	Diff. Input Slew Rate <sup>(2)</sup>	Measured differentially	0.4			V/ns
I <sub>IN</sub>	Diff. Input Leakage Current	$V_{IN} = V_{DD}, V_{IN} = GND$	-5	0.01	5	uA
$t_{DC}$	Diff. Input Duty Cycle	Measured differentially	45		55	%
tj <sub>c-c</sub>	Diff. Input Cycle to cycle jitter	Measured differentially			125	ps

#### Note:

- 1. Guaranteed by design and characterization, not 100% tested in production
- 2. Slew rate measured through +/-75 mV window centered around differential zero
- $3. \ The \ device can be \ driven \ by \ a single-ended \ clock \ by \ driving \ the \ true \ clock \ and \ biasing \ the \ complement \ clock \ input \ to \ the \ V bias, \ where \ V bias \ is \ (V_{IH}-V_{IL})/2$





### **HCSL Output Characteristics**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
V <sub>OH</sub>	Output Voltage High <sup>(1)</sup>	Statistical measurement on single-ended	660	784	850	mV
V <sub>OL</sub>	Output Voltage Low <sup>(1)</sup>	signal using oscilloscope math function	-150	_	150	mV
V <sub>OMAX</sub>	Output Voltage Maximum <sup>(1)</sup>	Measurement on single ended signal using	_	816	1150	mV
V <sub>OMIN</sub>	Output Voltage Minimum <sup>(1)</sup>	absolute value	-300	-42	_	mV
V <sub>OC</sub>	Output Cross Voltage <sup>(1,2,4)</sup>	_	250	430	550	mV
DV <sub>OC</sub>	V <sub>OC</sub> Magnitude Change <sup>(1,2,5)</sup>	_	_	12	140	mV

#### Note:

- 1. At default SMBUS amplitude settings.
- 2. Guaranteed by design and characterization—not 100% tested in production.
- 3. Measured from differential waveform.
- 4. This one is defined as voltage where Q+ = Q- measured on a component test board and only applied to the differential rising edge.
- 5. The total variation of all Vcross measurements in any particular system. This is a subset of Vcross\_min/max allowed.

### **HCSL Output AC Characteristics**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
f <sub>OUT</sub>	Output Frequency	_	50	100	133.33	MHz
BW	PLL Bandwidth <sup>(1,8)</sup>	-3dB point in high-bandwidth mode	1.3	3.2	3.6	MHz
БVV	PLL Bandwidtn(+)*/	-3dB point in low-bandwidth mode	0.7	1.7	1.9	MHz
tj <sub>peak</sub>	PLL Jitter Peaking <sup>(1)</sup>	Peak pass band gain	_	0.8	2	dB
	Slew Rate <sup>(1,2,3)</sup>	Scope averaging on fast setting	2.5	3.2	4.0	V/ns
$t_{RF}$	Siew Rate	Scope averaging on slow setting	2.2	3.0	3.7	V/ns
Dt <sub>RF</sub>	Slew Rate Matching <sup>(1,2,4)</sup>	Scope averaging on	_	7	15	%
t <sub>SKEW</sub>	Output Skew <sup>(1,2)</sup>	Averaging on, $V_T = 50\%$	_	11	50	ps
	D (1 D )	PLL Bypass mode, $V_T = 50\%$	2000	2500	3000	ps
t <sub>PDELAY</sub>	Propagation Delay	PLL mode, $V_T = 50\%$	-200	90	200	ps
$t_{DC}$	Duty Cycle <sup>(1,2)</sup>	Measured differentially, PLL mode	45	50	55	%
t <sub>DCD</sub>	Duty Cycle Distortion <sup>(1,7)</sup>	Measured differentially, PLL bypass mode @ 100MHz	-3.5	0	3.5	%
t <sub>DCD</sub>	Duty Cycle Distortion <sup>(1,7)</sup>	Measured differentially, SE input, PLL bypass mode @ 100MHz	-10	0	10	%
	0 1 (0 1 7)	PLL mode	_	14	50	ps
tj <sub>c-c</sub>	Cycle-to-Cycle Jitter <sup>(1,2)</sup>	Additive jitter, bypass mode	_	0.1	1	ps





### **HCSL Output AC Characteristics (Jitter)**

Symbol	Parameters	Condition	Min.	Тур.	Max.	Spec Limit	Units
		PCIe Gen 1 <sup>(6)</sup>	_	25	35	86	ps(p-p)
		PCIe Gen 2 Low Band, 10kHz < f < 1.5MHz		0.6	0.8	3	ps
		PCIe Gen 2 High Band, 1.5MHz < f < Nyquist (50MHz)	-	0.7	1.2	3.1	ps
	Integrated Phase Jitter PLL	PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)		0.25	0.4	1	ps
tj <sub>PHASEPLL</sub>	Mode (RMS) <sup>(1,5)</sup>	PCIe Gen 4 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)	_	0.25	0.4	0.5	ps
		PCIe Gen 5 <sup>(11)</sup> (PLL BW of 500k to 1.8MHz. CDR =20MHz)	_	0.07	0.12	0.15	ps
		125MHz, 1.5MHz to 20MHz, -20dB/ decade Rollover < 1.5MHz, -40dB/ decade rolloff > 10MHz		0.15 0.3	_	ps	
		133.33MHz	1	0.15	0.3	_	ps
		PCIe Gen 1	_	0.01	0.05	_	ps(p-p)
		PCIe Gen 2 Low Band, 10kHz < f < 1.5MHz		0.01	0.05	_	ps
		PCIe Gen 2 High Band, 1.5MHz < f < Nyquist (50MHz)	_	0.01	0.05	_	ps
		PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)		0.01	0.05	_	ps
tj <sub>PHASEA</sub>	Additive Integrated-Phase Jitter (RMS) <sup>(1,5,10)</sup>	PCIe Gen 4 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)	_	0.01	0.05	_	ps
		PCIe Gen 5 <sup>(11)</sup> (PLL BW of 500k to 1.8MHz. CDR =20MHz)	_	0.01	0.05	_	ps
		125MHz, 1.5MHz to 20MHz, -20dB/ decade Rollover < 1.5MHz, -40dB/ decade rolloff > 10MHz	_	0.01	0.05	_	ps
		133.33MHz		0.01	0.05	_	ps
		156.25MHz 12k to 20MHz		0.01	0.05		ps

#### Note

- 1. Guaranteed by design and characterization—not 100% tested in production.
- 2. Measured from differential waveform.
- 3. Slew rate is measured through the Vswing voltage range centered around differential 0V, within  $\pm 150 mV$  window.
- 4. Slew rate matching is measured through  $\pm 75 \text{mV}$  window centered around differential zero.
- 5. See http://www.pcisig.com for complete specs.
- 6. Sample size of at least 100k cycles. This can be extrapolated to 108ps pk-pk @ 1M cycles for a BER of 10<sup>-12</sup>.
- 7. Duty cycle distortion is the difference in duty cycle between the output and input clock when the device is operated in the PLL bypass mode.
- 8. The minimum and maximum values of each BW setting track each other, low BW max never occurs with high-BW minimum.
- 9. Applies to all differential outputs.
- 10. For additive jitter RMS value is calculated by the following equation = SQRT [(total jitter) $^{*2}$  (input jitter) $^{*2}$ ].
- 11. PCIe Gen 5 v0.9 specification.





### **SMBus Serial Data Interface**

PI6CB33201 is a slave-only device that supports block-read and block-write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer.

**Address Assignment** 

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	See SBMus Ado	1/0		

Note: SMBus address is latched on SADR pin

#### **How to Write**

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	1 bit
Start bit	Add.	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack	 Data Byte (N+X-1)	Ack	Stop bit

#### **How to Read**

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit
Start bit	Address	W(0)	Ack	Beginning Byte location = N	Ack	Repeat Start bit	Address	R(1)	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack

8 bits	1 bit	1 bit
Data Byte	NIA ala	Ston hit
 (N+X-1)	NAck	Stop bit





# **Byte 0: Output Enable Register**

Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1
7	Reserved	_	_	0		
6	Reserved	_	_	0		
5	Reserved	_	_	0		
4	Q1_OE	Q1 output enable	RW	1	See B11[1:0]	Pin control
3	Q0_OE	Q0 output enable	RW	1	See BII[I:0]	Pili collitoi
2	Reserved	_	_	0		
1	Reserved	_	_	0		
0	Reserved	_	_	0		

#### Note:

# Byte 1: PLL Operating Mode and Output Amplitude Control Register

Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	PLLMODERB1	PLL Mode Readback Bit1	R	Latch	Can DI I Omanat	ina Mada Tabla
6	PLLMODERB0	PLL Mode Readback Bit0	R	Latch	See PLL Operat	ing Mode Table
5	PLLMODE_SWCTR	Enable SW control of PLL Mode	RW	0	Values in B1[7:6] set PLL Mode	Values in B1[4:3] set PLL Mode
4	PLLMODE1	PLL Mode control Bit1	RW <sup>(1)</sup>	0	Can DLI Omanat	:
3	PLLMODE0	PLL Mode control Bit0	RW <sup>(1)</sup>	0	See PLL Operat	ing Mode Table
2	Reserved	_		1	_	_
1	Amplitude1	Control output amplitude	RW	1	'00' = 0.6V, '01' =	= 0.68V, '10' =
0	Amplitude0	Control output amplitude	RW	0	0.75V, '11' = 0.85	5V

#### Note:

1. B1[5] must be set to a 1 for these bits to have any effect on the part.

<sup>1.</sup> A low on these bits overrides the OE# pins and force the differential outputs to the state indicated by B11[1:0] (Low/Low default).





# Byte 2: Differential Output Slew Rate Control Register

Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	Reserved	_	_	1	_	_
6	Reserved	_	_	1	_	_
5	Reserved	_	_	1	_	_
4	SLEWRATECTR_Q1	Control slew rate of Q1	RW	1	Slow setting	Fast setting
3	SLEWRATECTR_Q0	Control slew rate of Q0	RW	1	Slow setting	Fast setting
2	Reserved	_	_	1	_	_
1	Reserved	_	_	1	_	_
0	Reserved	_	_	1	_	_

# **Byte 3: Frequency Select Control Register**

Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	Reserved	_	_	1	_	_
6	Reserved	_	_	1	_	_
5	FREQ_SEL_EN	Enable SW selection of frequency	RW	0	SW Freq. selection disabled	SW Freq. selection enabled
4	FSEL1	Freq. Select Bit 1	RW <sup>(1)</sup>	0	C F (	2.1 477.11
3	FSEL0	Freq. Select Bit 0	RW <sup>(1)</sup>	0	See Frequency S	Select Table
2	Reserved	_	_	1	_	_
1	Reserved	_	_	1	_	_
0	SLEWRATESEL FB	Adjust Slew Rate of Feedback signal	RW	1	Slow setting	Fast setting

#### Note:

# **Byte 4: Reserved**

Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1
7:0	Reserved	_	_	1	_	_

 $<sup>1.\</sup> B3[5]$  must be set to a 1 for these bits to have any effect on the part.





# Byte 5: Revision and Vendor ID Register

Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1	
7	RID3	Revision ID	R	0	· · · · · · · · · · · · · · · · · · ·		
6	RID2		R	0	rev = 0000		
5	RID1		R	0			
4	RID0		R	0			
3	PVID3		R	0			
2	PVID2	W 1 ID	R	0	Diodes = 0011		
1	PVID1	-	R	1			
0	PVID0		R	1			

# Byte 6: Device Type/Device ID Register

Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1
7	DTYPE1	Desire terms	RW	0	'00' = CG, '01' =	ZDB,
6	DTYPE0	Device type	RW	1	'10' = Reserve, '11' = ZDB	
5	DID5	]	RW	0		
4	DID4		RW	0		
3	DID3		RW	0	— 000010 binary, 02Hex	
2	DID2	Device ID	RW	0		
1	DID1		RW	1		
0	DID0		RW	0		

Byte 7: Reserved

Bit	<b>Control Function</b>	Description	Type	Power-up Condition	0	1
7:0	Reserved	_	_	0x08	_	_

# Byte 8 and 9: Reserved

Bit	<b>Control Function</b>	Description	Type	Power-up Condition	0	1
7:0	Reserved	_	_	B8 = 0x36 B9 = 0x00	_	_





**Byte 10: PD Restore** 

Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	Reserved	_	RW	1	_	_
6	PD Restore	PD Restore to default configuration	RW	1	Clear PD Config	Keep PD Config
5:0	Reserved	_	R	0	_	_

**Byte 11: Stop Control** 

Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	FB_imp[1]	Feedback Zout	RW	1	00=Reserved	10=100 DIF Zout
6	FB_imp[0]		RW	0	01=85 DIF Zout	11 = Reserved
5:2	Reserved	_	_	0	_	_
1	STP1	True/ Compliment DIF Output Disable Sate	RW	0	00= Low/Low	10= High/ Low
0	STP0		RW	0	01= HiZ/HiZ	11= Low/High

**Byte 12: Impedance Control** 

Bit	<b>Control Function</b>	Description	Type	Power-up Condition	0	1	
7	Q0_Zout1	Q0 Zout	RW				
6	Q0_Zout0	Q0 Zout	RW				
5	Reserved	_	RW		00 = Reserved		
4	Reserved	_	RW	10	$01 = 85\Omega$		
3	Reserved	_	RW	10	$10 = 100\Omega$ $11 = Reserved$		
2	Reserved	_	RW				
1	Reserved	_	RW				
0	Reserved	_	RW	1			





**Byte 13: Impedance Control** 

Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1
7	Reserved	_	RW	_		'
6	Reserved	_	RW			
5	Reserved	_	RW		00 = Reserved	
4	Reserved	_	RW	10	$01 = 85\Omega$	
3	Reserved	_	RW	10	$10 = 100\Omega$	
2	Reserved	_	RW		11 = Reserved	
1	Q1_Zout1	Q1 Zout	RW			
0	Q1_Zout0	Q1 Zout	RW			

**Byte 14: OE Termination Control** 

Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1
7	OE0_term1	OE0 Pull up or down	RW	0	00=None	10= Pullup
6	OE0_term0	OE0 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
5	Reserved	_	RW	0	_	_
4	Reserved	_	RW	1	_	_
3	Reserved	_	RW	0	_	_
2	Reserved	_	RW	1	_	_
1	Reserved	_	_	0	_	_
0	Reserved	_	_	1	_	_

**Byte 15: OE Termination Control** 

Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1
7	Reserved	_	RW	0	_	_
6	Reserved	_	RW	1	_	_
5	Reserved	_	RW	0	_	_
4	Reserved	_	RW	1	_	_
3	Reserved	_	_	0	_	_
2	Reserved	-	_	1	_	_
1	OE1_term1	OE1 Pullup or down	RW	0	00=None	10= Pullup
0	OE1_term0	OE1 Pullup or down	RW	1	01=Pulldown	11=Pullup and Down





**Byte 16: Power Good Termination Control** 

Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1
7:2	Reserved	_	_	0x00	_	_
1	PWRGD_PD1		RW	1	00=None	10= Pullup
0	PWRGD_PD0	Clock Power Good and Power Down Pull up or Pull down	RW	0	01=Pulldown	11=Pullup and Down

# Byte 17: Reserved

Bit	<b>Control Function</b>	Description	Type	Power-up Condition	0	1
7:0	Reserved	_	_	0	_	_

**Byte 18: Enable Pin Control** 

Syle 10. Enable 1 in Connor							
Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1	
7	Reserved	_	RW	0	_	_	
6	Reserved	_	RW	0	_	_	
5	Reserved	_		0	_	_	
4	OE1_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High	
3	OE0_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High	
2	Reserved	_	RW	0	_	_	
1	Reserved	_	RW	0	_	_	
0	Reserved	_	RW	0	_	_	

**Byte 19: Power Down Pin Control** 

Bit	<b>Control Function</b>	Function Description		Power-up Condition	0	1
7:1	Reserved	_	_	0	_	_
0	PWRGD_PD	PWRGD_PD Active via Pull up or Pull down	RW	0	Power Down = Low	Power Down = High

16





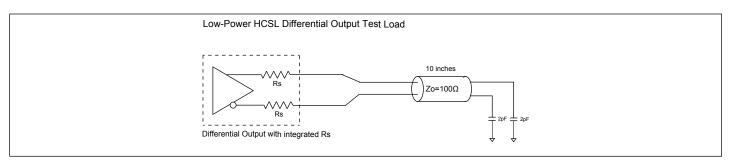


Figure 1. Low-Power HCSL Test Circuit

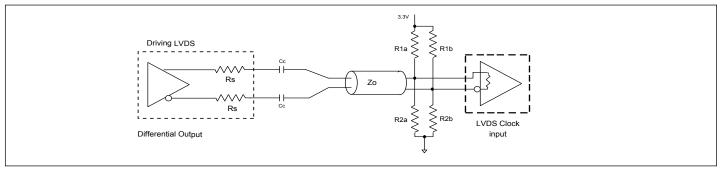


Figure 2. Differential Output Driving LVDS

# **Alternate Differential Output Terminations**

Component	Receiver with Termination	Receiver without Termination	Unit
$R_{1a}, R_{1b}$	10,000	140	Ω
$R_{2a}, R_{2b}$	5600	75	Ω
$C_{C}$	0.1	0.1	μF
$V_{CM}$	1.2	1.2	V

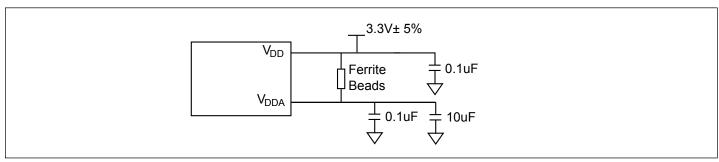


Figure 3. Power Supply Filter





### **Thermal Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$\theta_{JA}$	Thermal Resistance Junction to Ambient	Still air			54.4	°C/W
$\theta_{ m JC}$	Thermal Resistance Junction to Case				40.8	°C/W

# **Part Marking**

PI6CB33 201ZDIE ZYWXX

Z: Die Rev Y: Year

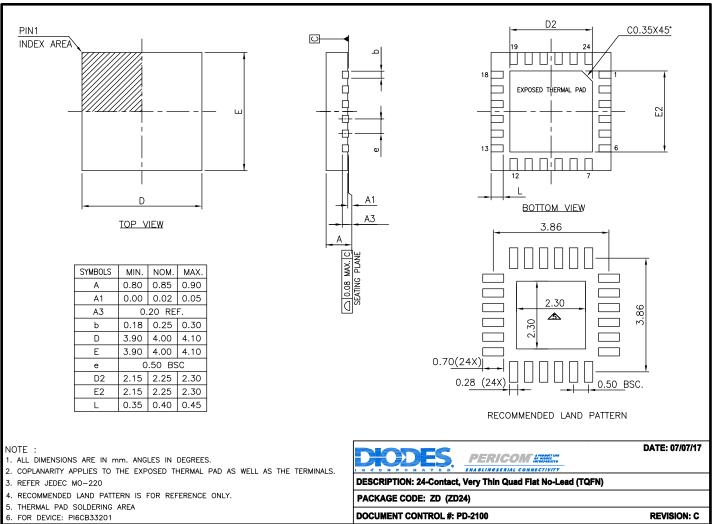
W: Workweek

1st X: Assembly Code 2nd X: Fab Code





## Packaging Mechanical: 24-TQFN (ZD)



#### For latest package information:

 $See \ http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.$ 

### Ordering Information

Ordering Code Package Code		Package Description	Pin 1 Location		
PI6CB33201ZDIEX	ZD	24-Contact, Very Thin Quad Flat No-Lead (TQFN)	Top Right Corner		
PI6CB33201ZDIEX-13R	ZD	24-Contact, Very Thin Quad Flat No-Lead (TQFN)	Top Left Corner		

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel
- 6. For packaging details, go to our website at: https://www.diodes.com/assets/MediaList-Attachments/Diodes-Package-Information.pdf





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- 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
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